

EMC Electronics Updates

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Location of the Front End electronics in the EMC barrel





21 Crystals Calorimeter Module (40 (phi) x (4+4) (theta) = 320 modules)







21 Front End Boards





Crystals Test Box







CsI (TI) test bench with different Integration time and shaping time

Csl:

CSP Cremat integr. time = 140 µs shaping time = 500 ns CSP Hamamatsu integr.time = 100 ns + shaping time = 100 ns





We use a modified version of our VFE shaper design for LYSO With different hybrid CSP Cremat (fixed integration time) Hamamatsu(flexible integration time) And different shaping time.

Barrel Front End Replacemet



2 Pin Diode readout2 Channel2 different Gain x1 x32

We have done a meeting with Italian Texas Instruments Field Application Engineer to create a grid of possible components candidate for a new Front Ends design with shorter integration time (hundreds of ns instead of microseconds) and shorter shaping time.

- LDO(TPS7A49) to filter and regulate voltage
- Input FET (BF862)
- CSP OPAMP (LMH6624 100mW alone under decision)
- Shaper OPAMP (OPA836)
- Differential driver (THS4521)

Using off the shelf components give the possibility to have access to best professional design but general purpose meaning more functionality -> more power consumption. With the components proposed we have 170 mW/Crystal instead of 100 mW/Crystal of Babar design.

Location of the DTU mini crate in the EMC barrel





Mini Crate structure





Digitizer Board



Forward Calorimeter BGO Study

Same setup using the Crystal test box.

Comparison of two CSP (Cremat and Hamamatsu using the same integration time)

BGO with ¹³⁷Cs source

Comparison with source: Hamamatsu vs Cremat



Analysis from P. Gauzzi

BGO - APD signal

Bin by bin average over 50000 waveforms

- CSP Hamamatsu i.t.= 1 μs s.t. = 500 ns FWHM =1.2 μs
- CSP Cremat i.t. = 140 μs s.t. = 500 ns FWHM = 1.4 μs



BGO - Setting the energy scale

BGO activity due to ²⁰⁷Bi contamination (decays to ²⁰⁷Pb, with 4 γ lines)



[from Lewis, NIMA264(1988)534]



P.Gauzzi

Comparison S/N ratio BGO(crystal test box) vs LYSO (BTF tests)

Electronic noise

- BTF test with LYSO crystal ⇒ electronic noise was ~ 250 keV
- Lab test of BGO ⇒ 1.5 2 MeV

 $\frac{Noise(BGO)}{Noise(BTF)} = \frac{LY_{LYSO}}{LY_{BGO}} \frac{G_{APD}(BGO)}{G_{APD}(BTF)} \frac{1}{Atten_{BTF}} =$

$$=rac{75}{9}$$
 $rac{1}{4}$ $rac{1}{0.175}\simeq 10$



• Random trigger

Oscilloscope noise

 $\sigma = 0.49 \Rightarrow ~ 300 \text{ keV}$

LYSO signal is better BGO needs better electronics noise



Conclusions

- •The Mechanical structure of the Barrel give some strong physical constraint to electronics design.
- •The Integration time and shaping time is under study with physics simulation and on field measuraments using our Crystal test box.
- •The Front-END CSP preaplifier design study was started using COTS components strong interaction with TI FAI.
- •The new power dissipation budget seems higher respesct to Babar
- •Digitizer board starting to found COTS (first interaction with TI FAI)
- •Forward crystal evaluation (BGO,LYSO) proceed with interesting results
- •Power Supply request questionaire can be started to fill using some infomation above